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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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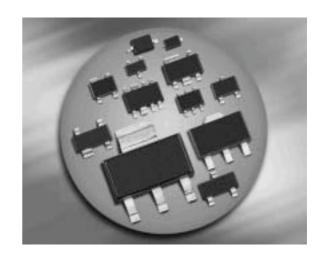


Silicon Low Leakage Diode

- Low-leakage applications
- Medium speed switching times
- Series pair configuration
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101







BAV199



Туре	Package	Configuration	Marking	
BAV199	SOT23	series	JYs	

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V _R	80	V	
Peak reverse voltage	V _{RM}	85		
Forward current	/ _F	200	mA	
Non-repetitive peak surge forward current	I _{FSM}		Α	
$t = 1 \mu s$		4.5		
t = 1 s		0.5		
Total power dissipation	P _{tot}	330	mW	
BAV199, <i>T</i> _S ≤ 31°C				
Junction temperature	T _i	150	°C	
Storage temperature	T _{stq}	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	≤ 360	K/W
BAV199			

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¹Pb-containing package may be available upon special request

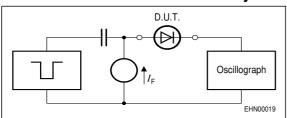
²For calculation of *R*_{thJA} please refer to Application Note Thermal Resistance



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics		т.			
Breakdown voltage	$V_{(BR)}$	85	-	-	V
$I_{(BR)} = 100 \mu A$					
Reverse current	I _R				nA
$V_{\rm R} = 75 \text{ V}$		-	-	5	
$V_{R} = 75 \text{ V}, \ T_{A} = 150 \text{ °C}$		-	-	80	
Forward voltage	V_{F}				mV
$I_{F} = 1 \; mA$		-	-	900	
$I_{\rm F} = 10 \text{mA}$		-	-	1000	
$I_{F} = 50 \; mA$		_	-	1100	
$I_{\rm F} = 150 \text{mA}$		-	-	1250	
AC Characteristics					•
Diode capacitance	C_{T}	-	2	-	pF
$V_{R} = 0 \text{ V}, f = 1 \text{ MHz}$					
Reverse recovery time	<i>t</i> _{rr}	-	0.6	1.5	μs
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured at $I_{\rm R}$ = 1mA ,					
$R_{\rm L}$ = 100 Ω					

Test circuit for reverse recovery time



Pulse generator: $t_p = 10 \mu s$, D = 0.05, $t_r = 0.6 ns$,

 $R_{\rm i} = 50\Omega$

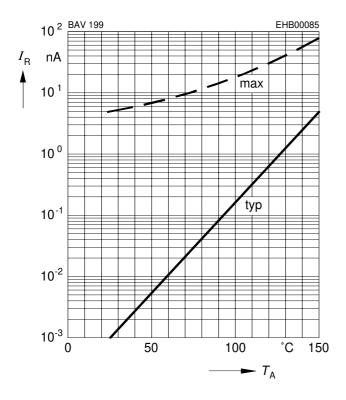
Oscillograph: $R = 50\Omega$, $t_{\rm r} = 0.35 {\rm ns}$, $C \le 1 {\rm pF}$

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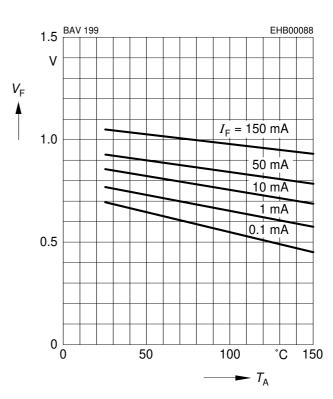
Reverse current $I_R = f(T_A)$

$$V_{R} = 70V$$



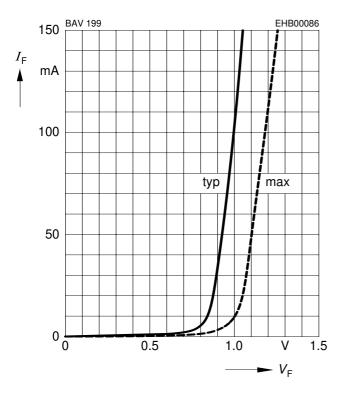
Forward Voltage $V_F = f(T_A)$

 $I_{\mathsf{F}} = \mathsf{Parameter}$



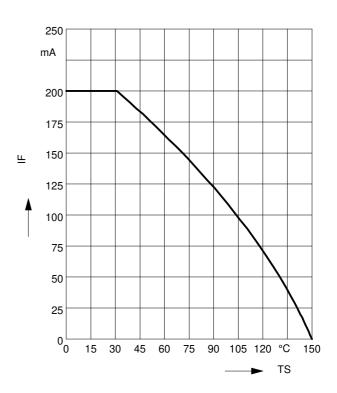
Forward current $I_F = f(V_F)$

$$T_{\mathsf{A}} = 25^{\circ}\mathsf{C}$$



Forward current $I_F = f(T_S)$

BAV199



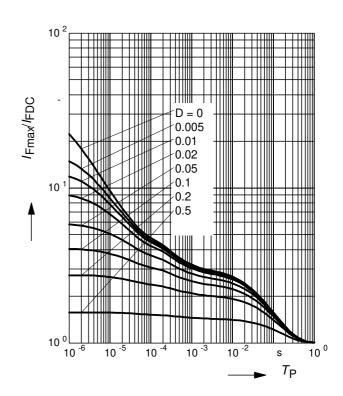


Permissible Puls Load $R_{thJS} = f(t_p)$

10 ³ 10² **A**thJS 10 ¹ 0,2 0,1 0,05 0,02 0,01 ₩0,0 0,005 10 -4 10 ⁰ 10 10 10 T_{P}

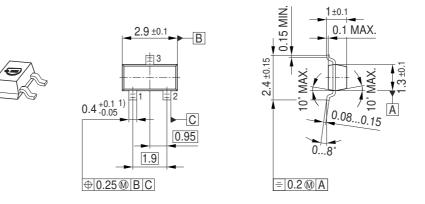
Permissible Pulse Load

$$I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$$



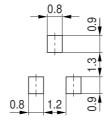


Package Outline

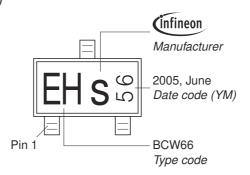


Foot Print



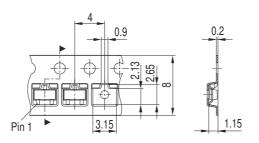


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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